



## DOCUMENT CHANGE REQUEST

DCR number	1582	Changes required for:	General	Originator:	Steve Thacker
Date:	2023/09/12	Date sent:	2023/06/28	Organisation:	ESCC Executive Secretariat
Status:	IMPLEMENTED				

Title: TRANSISTORS, POWER, MOSFET, N CHANNEL, RAD-HARD BASED ON TYPES BUY06CS35J-01,

Number: 5205/032 Issue: 2

Other documents affected:

Page:

Various; see attached

Paragraph:

Various; see attached & below

Original wording:

As per 5205/032 issue 2

Proposed wording:

Amend, for Variant 06 only, the maximum Static Drain-to-Source On Resistance,  $r_{DS(on)}$ , throughout this specification; to be as follows (see attached for details, with changes highlighted yellow):

a) In Para. 1.4.2, 2.5.1, 2.6, 2.7, 2.11.2:

Variant 06: change maximum limit for  $r_{DS(on)}$  to be 7mohm (was 6.5mohm)

b) In Para. 2.5.2:

Variant 06: change maximum limit for  $r_{DS(on)}$  to be 10.5mohm (was 10mohm)

Justification:

This DCR is raised on behalf of Manufacturer Infineon.

Infineon stated that, as previously discussed with ESA/Tesat/DLR, this marginal increase in maximum  $r_{DS(on)}$  is required for the new (in 2023) Variant 06 due to:

"a shift of the  $r_{DS(on)}$  distribution towards higher values (for new Variant 06 only). However we (Infineon) do not see any impact on the reliability of the device".

Attachments:

esc5205032iss\_draft\_3a\_for\_review.docx

Modifications:

N/A

Approval signature:



Date signed:

2023-09-12